

PATENT APPLICATION
Docket No. 2522-040
Client No. AW8072US/MJ

Applicant: Jac-Jong HAN, Yong-Woo HYUNG, Seung-Mok SHIN, Kong-Soo LEE and Eun-Jung YUN
Filing Date: September 26, 2003 Group: ~~not yet assigned~~ 2823
Serial No. ~~not yet assigned~~ 10/672,884 Examiner: ~~not yet assigned~~ H. Lee
Title: METHOD OF FORMING A GATE ELECTRODE, METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING THE GATE ELECTRODE, AND METHOD OF OXIDIZING A SUBSTRATE

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub Class
_____	_____	/				

FOREIGN PATENT DOCUMENTS

Exam Init	Ref	Document Number	Publication Date	Country	Name
<u>Lu</u>	_____	JP8032066	2/2/1996	Japan	Katsuichi
<u>Lu</u>	_____	JP11345970	12/14/1999	Japan	Tomio et al.

OTHER DOCUMENTS

Exam Init	Ref	Author, Title, Date, Pertinent Pages, Etc.)
<u>Lu</u>	_____	English language of Abstract for Japanese Patent Publication No. JP8032066, filed 2/2/1996.
<u>Lu</u>	_____	English language of Abstract for Japanese Patent Publication No. JP11345970, filed 12/14/1999.

Examiner: Seun-Ming Lee

Date Considered: 6/17/04